

Surface Micromachined Accelerometer

Introduction

This example shows how to model a surface micromachined accelerometer in COMSOL, using the electromechanics interface. The example is based on the case study in Ref. 1. The model also demonstrates the use of linked subsequences. A collection of geometric building blocks can be stored in a source model file as subsequences. Thereafter, other model files can reuse the same building blocks by linking to the subsequences in the source model file. Each subsequence can take arguments to generate a building block with specific dimensions or number of features. In this model, a surface micromachined accelerometer is created from three building blocks, two of which are used multiple times by calling the corresponding subsequence with different arguments.

Model Definition

The surface micromachined accelerometer is composed of a released proof mass supported by anchored springs at its two ends, together with sensing and self test electrodes extending to the sides. When the device is subject to an acceleration, the restoring force from the springs gives a displacement of the proof mass in proportion to the acceleration. The displacement causes a change in the capacitance between the fixed and moving electrodes. This change in capacitance can be measured with a number of standard circuits.

For acceleration along the axis of the accelerometer, symmetry allows modeling only half of the geometry for faster computation. The three geometric building blocks are the proof mass with attached electrodes (Figure 1), the folded spring (Figure 2), and the fixed electrode array (Figure 3). These building blocks are implemented as Subsequences that take arguments to specify dimensions, orientation, position, and number of features. For example, the proof mass shown in Figure 1 has 7 sense electrodes at the center and 3 self test electrodes at each end. The actual model on the other hand is built with 21 sense electrodes, by calling the same Subsequence with the corresponding argument 21. As another example, Figure 4 shows an electrode array built from the same Subsequence as in Figure 3, with a different set of arguments, resulting in different number of electrodes, dimensions, and orientation of the anchor pads.

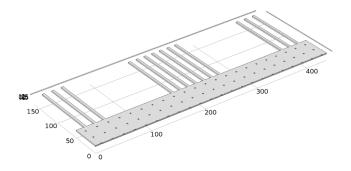


Figure 1: Building block for the proof mass with attached electrodes. Grid scales are in micrometers.

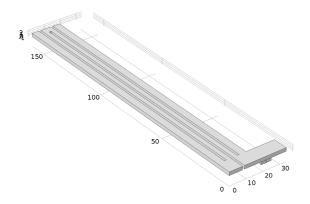


Figure 2: Building block for the folded spring. Grid scales are in micrometers.

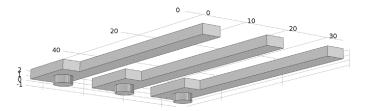


Figure 3: Building block for the fixed electrode array. Grid scales are in micrometers.

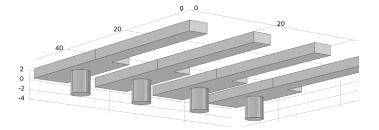


Figure 4: Example of an electrode array built from the same Subsequence as in Figure 3, with a different set of arguments. Grid scales are in micrometers.

The geometry sequence begins by calling the proof mass Subsequence, followed by calling the folded spring Subsequence twice to attach a spring at each end of the proof mass. Subsequently 6 calls to the fixed electrode array Subsequence are made to construct the sense and self test fixed electrodes.

Each Subsequence call contributes to a domain and a boundary selection. This allows easy assignment of domain physics and boundary conditions in the physics interface.

The model uses polysilicon for the building material and includes a rectangular air domain surrounding the polysilicon. The Electromechanics multiphysics interface models the electric field within the deforming gaps between the electrodes, and applies the appropriate electrostatic forces to the solids, which creates a corresponding structural deformation. The deformation of the gaps between electrodes results in nonlinear geometrical effects, which are included in the Electromechanics multiphysics interface by default.

The entire polysilicon solid is subject to an acceleration using the Body Load domain physics feature. The (mechanically) fixed electrodes are set at constant potentials, and the proof mass (and its attached electrodes) is at a floating potential whose value will be determined by the position-dependent capacitance (and the applied voltages on the fixed sense electrodes).

Results and Discussion

The first study illustrates the normal operation of the accelerometer by sweeping the applied acceleration from -50 to +50 g and computing the resulting displacement of the proof mass. Figure 5 shows the displacement of the polysilicon domains when the applied acceleration is 50 g. The proof mass (and the attached moving electrodes) moves by about

0.07 micrometer. The anchored spring bases and the fixed electrodes have very little movement. The folded springs have varying displacement along its length as expected.

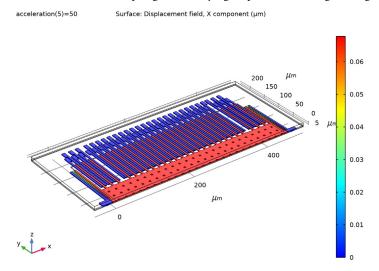


Figure 5: Displacement of the polysilicon domains when the applied acceleration is 50 g. The proof mass moves by about 0.07 micrometer. The anchored spring bases and the fixed electrodes have very little movement. The springs have varying displacement along its length as expected.

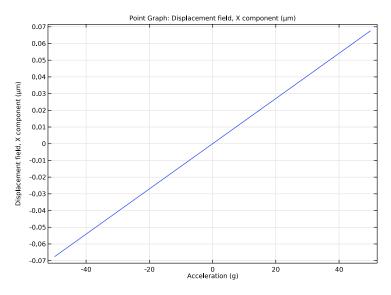


Figure 6: Displacement vs acceleration.

Figure 6 shows the linear relationship between the displacement and the applied acceleration. The displacement is measured via the capacitive coupling between the moving and the fixed sense electrodes. In the real device, during normal operation, the proof mass with its attached moving electrodes is floating at a potential close to one half of the supply voltage, and a high frequency square wave swinging between zero and the full supply voltage is applied with opposite phase to the fixed sense electrodes on each side of the moving electrodes. The fixed self test electrodes are biased at one half of the supply voltage. When the proof mass moves as a result of the acceleration, an alternating voltage in proportion to the displacement is induced due to the capacitive coupling between the fixed and moving electrodes. This arrangement nulls the average electrostatic force between the fixed and moving sense electrodes, and facilitates easier signal processing in the attached circuitry. In this example the stationary part of the square wave is modeled using a stationary study, so that the problem solves relatively quickly. The bias is shifted to zero for convenience, and the amplitude of the square wave is divided by an artificial factor of 1000 to reduce the electrostatic force between the fixed and moving sense electrodes (in practice the time average of the force will be zero due to the high frequency excitation). For a 5 V supply in the physical device, this corresponds to applying a $\pm/-2.5$ mV on the right-side and left-side fixed sense electrodes in the model. In postprocessing, the artificial factor of 1000 is multiplied back to the sensed voltage of the proof mass. Figure 7 shows

the linear relationship between the sense voltage and the acceleration. This signal is fed into an amplifier that in the real device was built on the same substrate as the mechanical structure.

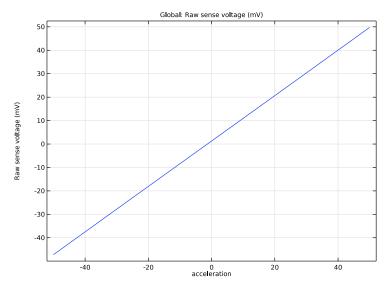


Figure 7: Sensed voltage vs. applied acceleration.

The accelerometer in the model was designed with self test electrodes that could be employed to calibrate the device in the factory. The second study illustrates the self testing by applying a bias of 2 V on the fixed self test electrodes, which are at the side of the moving electrodes attached to the proof mass. The electric field between the fixed and the moving electrodes exerts an electrostatic force that causes the proof mass to move. Figure 8 shows the displacement of the polysilicon domains when 0 V is applied to the fixed self test electrodes on the left-hand side of the moving electrodes attached to the proof mass, and 2 V to those on the right-hand side. The proof mass moves by about 0.02 μ m, which is large enough in magnitude for the self test purpose (compared to the 0.07 μ m of full range displacement shown in Figure 5 and Figure 6).

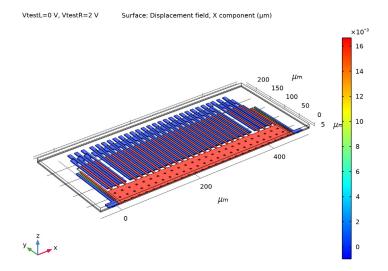


Figure 8: Displacement of the polysilicon domains when 0 V is applied to the fixed self test electrodes on the left side of the moving electrodes attached to the proof mass, and 2 V to those on the right side. The proof mass moved by about $0.02 \,\mu$ m, which is large enough in magnitude for the self test purpose (compared to the 0.07 μ m of full range displacement shown in Figure 5 and Figure 6).

Figure 9 compares the displacement obtained from applying the self test voltage to each side of the fixed electrodes. The displacement values have the same magnitude with opposite signs, as expected from symmetry.

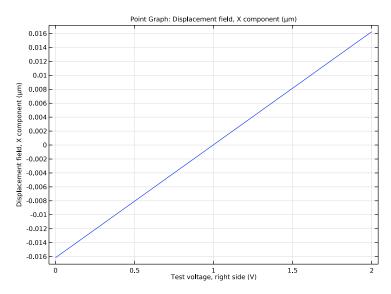


Figure 9: Displacement vs. applied self test voltage.

Reference

1. S.D. Senturia, *Microsystem Design* 5th ed., Kluwer Academic Publishers, pp. 513–525, 2003.

Application Library path: MEMS_Module/Sensors/ surface_micromachined_accelerometer

Modeling Instructions

ROOT

Load the geometry file.

I From the File menu, choose Open.

2 Browse to the model's Application Libraries folder and double-click the file surface_micromachined_accelerometer_geom_sequence.mph.

The model geometry has been set up using parts in a linked file. It is easier to visualize with wireframe rendering.

COMPONENT I (COMPI)

- I Click the 🗮 Wireframe Rendering button in the Graphics toolbar.
- **2** Click the **Joom Extents** button in the **Graphics** toolbar.

ADD MATERIAL

- I In the Home toolbar, click 🙀 Add Material to open the Add Material window.
- **2** Go to the **Add Material** window.
- 3 In the tree, select Built-in>Air.
- 4 Click 间 Add to Component I (compl).
- 5 In the tree, select MEMS>Semiconductors>Si Polycrystalline silicon.
- 6 Click 间 Add to Component I (compl).
- 7 In the Home toolbar, click 🙀 Add Material to close the Add Material window.

MATERIALS

- Si Polycrystalline silicon (mat2)
- I In the Settings window for Material, locate the Geometric Entity Selection section.
- 2 From the Selection list, choose Polysilicon.

DEFINITIONS

All domains

- I In the **Definitions** toolbar, click **here Explicit**.
- 2 In the Settings window for Explicit, type All domains in the Label text field.
- 3 Locate the Input Entities section. Select the All domains check box.

Air

- I In the **Definitions** toolbar, click **Difference**.
- 2 In the Settings window for Difference, type Air in the Label text field.
- 3 Locate the Input Entities section. Under Selections to add, click + Add.
- 4 In the Add dialog box, select All domains in the Selections to add list.
- 5 Click OK.

- 6 In the Settings window for Difference, locate the Input Entities section.
- 7 Under Selections to subtract, click + Add.
- 8 In the Add dialog box, select Polysilicon in the Selections to subtract list.
- 9 Click OK.

Deforming Domain 1

- I In the Model Builder window, expand the Component I (compl)>Definitions>Moving Mesh node, then click Deforming Domain I.
- 2 In the Settings window for Deforming Domain, locate the Domain Selection section.
- 3 From the Selection list, choose Air.

SOLID MECHANICS (SOLID)

I In the Model Builder window, under Component I (compl) click Solid Mechanics (solid).

- 2 In the Settings window for Solid Mechanics, locate the Domain Selection section.
- **3** From the Selection list, choose Polysilicon.

Body Load I

- I In the Physics toolbar, click 📄 Domains and choose Body Load.
- 2 In the Settings window for Body Load, locate the Force section.
- **3** Specify the $\mathbf{F}_{\mathbf{V}}$ vector as

acceleration*solid.rho*g_const	x
0	у
0	z

4 Locate the Domain Selection section. From the Selection list, choose Polysilicon.

Fixed Constraint I

- I In the Physics toolbar, click 📄 Boundaries and choose Fixed Constraint.
- 2 In the Settings window for Fixed Constraint, locate the Boundary Selection section.
- 3 From the Selection list, choose Anchor plane.

Symmetry 1

- I In the Physics toolbar, click 📄 Boundaries and choose Symmetry.
- 2 In the Settings window for Symmetry, locate the Boundary Selection section.
- **3** From the Selection list, choose Symmetry plane.

DEFINITIONS

Symmetry/Roller 1

- I In the Model Builder window, under Component I (compl)>Definitions>Moving Mesh click Symmetry/Roller I.
- 2 In the Settings window for Symmetry/Roller, locate the Boundary Selection section.
- 3 From the Selection list, choose Symmetry plane.

ELECTROSTATICS (ES)

In the Model Builder window, under Component I (compl) click Electrostatics (es).

Charge Conservation, Air

- I In the Physics toolbar, click 🔚 Domains and choose Charge Conservation.
- 2 In the Settings window for Charge Conservation, type Charge Conservation, Air in the Label text field.
- 3 Locate the Domain Selection section. From the Selection list, choose Air.

Ground I

- I In the Physics toolbar, click 🔚 Boundaries and choose Ground.
- 2 Select Boundary 45 only.

Sense Terminal L

- I In the Physics toolbar, click 🔚 Boundaries and choose Terminal.
- 2 In the Settings window for Terminal, type Sense Terminal L in the Label text field.
- **3** Locate the **Boundary Selection** section. From the **Selection** list, choose **Sense left boundaries**.
- 4 Locate the Terminal section. From the Terminal type list, choose Voltage.
- **5** In the V_0 text field, type -2.5[mV].

Sense Terminal R

- I In the Physics toolbar, click 🔚 Boundaries and choose Terminal.
- 2 In the Settings window for Terminal, type Sense Terminal R in the Label text field.
- **3** Locate the **Boundary Selection** section. From the **Selection** list, choose **Sense right boundaries**.
- **4** Locate the **Terminal** section. From the **Terminal type** list, choose **Voltage**.
- **5** In the V_0 text field, type 2.5[mV].

Floating Potential 1

- I In the Physics toolbar, click 🔚 Boundaries and choose Floating Potential.
- 2 In the Settings window for Floating Potential, locate the Boundary Selection section.
- 3 From the Selection list, choose Proof mass boundaries.

Self Test Terminal L

- I In the Physics toolbar, click 🔚 Boundaries and choose Terminal.
- 2 In the Settings window for Terminal, type Self Test Terminal L in the Label text field.
- **3** Locate the **Boundary Selection** section. From the **Selection** list, choose **Self test left boundaries**.
- 4 Locate the Terminal section. From the Terminal type list, choose Voltage.
- **5** In the V_0 text field, type VtestL.

Self Test Terminal R

- I In the Physics toolbar, click 🔚 Boundaries and choose Terminal.
- 2 In the Settings window for Terminal, type Self Test Terminal R in the Label text field.
- **3** Locate the **Boundary Selection** section. From the **Selection** list, choose **Self test right boundaries**.
- 4 Locate the Terminal section. From the Terminal type list, choose Voltage.
- **5** In the V_0 text field, type VtestR.

MESH I

Free Triangular 1

- I In the Mesh toolbar, click \bigwedge Boundary and choose Free Triangular.
- 2 In the Settings window for Free Triangular, locate the Boundary Selection section.
- 3 From the Selection list, choose Meshing plane.
- 4 Click 🖷 Build Selected.

Swept I

In the Mesh toolbar, click 🦓 Swept.

Distribution I

- I Right-click Swept I and choose Distribution.
- 2 In the Settings window for Distribution, locate the Domain Selection section.
- 3 Click Clear Selection.
- 4 Select Domain 3 only.

- 5 Locate the Distribution section. In the Number of elements text field, type 1.
- 6 Click 📗 Build All.

STUDY I: NORMAL OPERATION

- I In the Model Builder window, right-click Study I and choose Rename.
- 2 In the **Rename Study** dialog box, type **Study 1:** Normal Operation in the **New label** text field.
- 3 Click OK.

Step 1: Stationary

- I In the Model Builder window, expand the Study I: Normal Operation node, then click Step I: Stationary.
- 2 In the Settings window for Stationary, click to expand the Results While Solving section.
- **3** Select the **Plot** check box.
- 4 From the Update at list, choose Steps taken by solver.
- 5 Click to expand the Study Extensions section. Select the Auxiliary sweep check box.
- 6 Click + Add.
- 7 Click Range.
- 8 In the Range dialog box, type -50 in the Start text field.
- 9 In the Step text field, type 25.
- **IO** In the **Stop** text field, type **50**.
- II Click Add.

Solution 1 (soll)

- I In the Study toolbar, click **here** Show Default Solver.
- 2 In the Model Builder window, expand the Solution I (soll) node.
- 3 In the Model Builder window, expand the Study 1: Normal Operation> Solver Configurations>Solution 1 (sol1)>Dependent Variables 1 node, then click Spatial mesh displacement (compl.spatial.disp).
- 4 In the Settings window for Field, locate the Scaling section.
- 5 In the Scale text field, type 1e-7.
- 6 In the Model Builder window, click Displacement field (compl.u).
- 7 In the Settings window for Field, locate the Scaling section.
- 8 In the Scale text field, type 1e-7.

- 9 In the Model Builder window, click Electric potential (compl.V).
- 10 In the Settings window for Field, locate the Scaling section.
- II From the Method list, choose Manual.
- **12** In the **Scale** text field, type 1e-3.
- **I3** In the Model Builder window, click Floating potential (compl.es.fpl.V0_ode).
- 14 In the Settings window for State, locate the Scaling section.
- I5 From the Method list, choose Manual.
- **I6** In the **Scale** text field, type **5e-5**.
- I7 In the Model Builder window, expand the Study 1: Normal Operation>Solver Configurations>Solution 1 (sol1)>Stationary Solver 1>Segregated 1 node.
- **18** Right-click **Electric potential** and choose **Move Down**.
- **19** Right-click **Electric potential** and choose **Move Down**.
- **20** In the **Study** toolbar, click **= Compute**.

RESULTS

Surface 1

- I In the Model Builder window, expand the Displacement (solid) node, then click Surface I.
- 2 In the Settings window for Surface, locate the Expression section.
- **3** In the **Expression** text field, type u.
- 4 In the Displacement (solid) toolbar, click **I** Plot.

Multislice I

- I In the Model Builder window, expand the Electric Potential (es) node, then click Multislice I.
- 2 In the Settings window for Multislice, locate the Expression section.
- 3 From the Unit list, choose mV.
- 4 Locate the Multiplane Data section. Find the x-planes subsection. In the Planes text field, type 0.
- 5 Find the y-planes subsection. In the Planes text field, type 0.
- 6 In the Electric Potential (es) toolbar, click 🗿 Plot.

ID Plot Group 4

In the Home toolbar, click 🚛 Add Plot Group and choose ID Plot Group.

Point Graph 1

- I Right-click ID Plot Group 4 and choose Point Graph.
- **2** Select Point 65 only.
- 3 In the Settings window for Point Graph, locate the y-Axis Data section.
- 4 In the Expression text field, type u.

Displacement vs. Acceleration

- I In the Model Builder window, right-click ID Plot Group 4 and choose Rename.
- 2 In the Rename ID Plot Group dialog box, type Displacement vs. Acceleration in the New label text field.
- 3 Click OK.
- 4 In the Settings window for ID Plot Group, locate the Plot Settings section.
- 5 Select the x-axis label check box.
- 6 In the associated text field, type Acceleration (g).
- 7 In the Displacement vs. Acceleration toolbar, click 🗿 Plot.

ID Plot Group 5

In the Home toolbar, click 📠 Add Plot Group and choose ID Plot Group.

Global I

- I Right-click ID Plot Group 5 and choose Global.
- 2 In the Settings window for Global, locate the y-Axis Data section.
- **3** In the table, enter the following settings:

Expression	Unit	Description
es.fp1.V0*1000	mV	Raw sense voltage

- 4 Click to expand the Legends section. Clear the Show legends check box.
- 5 In the ID Plot Group 5 toolbar, click 💽 Plot.

Sense V vs. Acceleration

- I In the Model Builder window, right-click ID Plot Group 5 and choose Rename.
- 2 In the Rename ID Plot Group dialog box, type Sense V vs. Acceleration in the New label text field.
- 3 Click OK.

ADD STUDY

I In the Home toolbar, click ~ 2 Add Study to open the Add Study window.

- **2** Go to the **Add Study** window.
- 3 Find the Studies subsection. In the Select Study tree, select General Studies>Stationary.
- 4 Click + Add Study.
- 5 In the Home toolbar, click \sim Add Study to close the Add Study window.

STUDY 2

Step 1: Stationary

- I In the Settings window for Stationary, locate the Study Extensions section.
- 2 Select the Auxiliary sweep check box.
- 3 Click + Add.
- **4** In the table, enter the following settings:

Parameter name	Parameter value list	Parameter unit
VtestL (Test voltage, left side)	2 0	V

5 Click + Add.

6 In the table, enter the following settings:

Parameter name	Parameter value list	Parameter unit
VtestR (Test voltage, right side)	0 2	V

- 7 From the Run continuation for list, choose No parameter.
- 8 In the Model Builder window, right-click Study 2 and choose Rename.
- 9 In the Rename Study dialog box, type Study 2: Self Test in the New label text field.

IO Click OK.

Solution 2 (sol2)

- I In the Study toolbar, click **here** Show Default Solver.
- 2 In the Model Builder window, expand the Solution 2 (sol2) node.
- 3 In the Model Builder window, expand the Study 2: Self Test>Solver Configurations> Solution 2 (sol2)>Dependent Variables 1 node, then click Spatial mesh displacement (comp1.spatial.disp).
- 4 In the Settings window for Field, locate the Scaling section.
- 5 In the Scale text field, type 1e-8.
- 6 In the Model Builder window, click Displacement field (compl.u).
- 7 In the Settings window for Field, locate the Scaling section.

- 8 In the Scale text field, type 1e-8.
- 9 In the Model Builder window, click Electric potential (compl.V).
- 10 In the Settings window for Field, locate the Scaling section.
- II From the Method list, choose Manual.
- **12** In the **Scale** text field, type 1.
- I3 In the Model Builder window, click Floating potential (compl.es.fpl.V0_ode).
- 14 In the Settings window for State, locate the Scaling section.
- 15 From the Method list, choose Manual.
- **I6** In the **Scale** text field, type **0.1**.
- **I7** In the **Study** toolbar, click **= Compute**.

RESULTS

Surface 1

- I In the Model Builder window, expand the Displacement (solid) I node, then click Surface I.
- 2 In the Settings window for Surface, locate the Expression section.
- 3 In the Expression text field, type u.
- 4 In the Displacement (solid) I toolbar, click 🗿 Plot.
- **5** Click the **F Zoom Extents** button in the **Graphics** toolbar.

Multislice 1

- I In the Model Builder window, expand the Electric Potential (es) I node, then click Multislice I.
- 2 In the Settings window for Multislice, locate the Multiplane Data section.
- 3 Find the x-planes subsection. In the Planes text field, type 0.
- 4 Find the y-planes subsection. In the Planes text field, type 0.
- 5 In the Electric Potential (es) I toolbar, click 💽 Plot.

ID Plot Group 9

- I In the Home toolbar, click 📠 Add Plot Group and choose ID Plot Group.
- 2 In the Settings window for ID Plot Group, locate the Data section.
- 3 From the Dataset list, choose Study 2: Self Test/Solution 2 (sol2).

Point Graph 1

I Right-click ID Plot Group 9 and choose Point Graph.

- **2** Select Point 65 only.
- 3 In the Settings window for Point Graph, locate the y-Axis Data section.
- 4 In the Expression text field, type u.
- 5 Locate the x-Axis Data section. From the Parameter list, choose Expression.
- 6 In the Expression text field, type VtestR.
- 7 In the ID Plot Group 9 toolbar, click 🗿 Plot.

Displacement vs. Self Test V

- I In the Model Builder window, right-click ID Plot Group 9 and choose Rename.
- 2 In the Rename ID Plot Group dialog box, type Displacement vs. Self Test V in the New label text field.
- 3 Click OK.

Appendix — Geometry Instructions

From the File menu, choose New.

NEW

In the New window, click Model Wizard.

MODEL WIZARD

- I In the Model Wizard window, click 间 3D.
- 2 In the Select Physics tree, select Structural Mechanics>Electromagnetics-Structure Interaction>Electromechanics>Electromechanics.
- 3 Click Add.
- 4 Click \bigcirc Study.
- 5 In the Select Study tree, select General Studies>Stationary.
- 6 Click 🗹 Done.

GEOMETRY I

- I In the Geometry toolbar, click \land Parts and choose Load Part.
- 2 Browse to the model's Application Libraries folder and double-click the file surface_micromachined_accelerometer_geom_subsequence.mph.
- **3** In the Load Part dialog box, in the Select parts list, choose Proof mass with fingers, Spring and anchor, and Electrode array.
- 4 Click OK.

GLOBAL DEFINITIONS

Parameters 1

- I In the Model Builder window, under Global Definitions click Parameters I.
- 2 In the Settings window for Parameters, locate the Parameters section.
- 3 Click 📂 Load from File.
- 4 Browse to the model's Application Libraries folder and double-click the file surface_micromachined_accelerometer_parameters.txt.

GEOMETRY I

Part Link: Proof mass

- I In the Geometry toolbar, click \bigtriangleup Parts and choose Proof mass with fingers.
- 2 In the Settings window for Part Instance, type Part Link: Proof mass in the Label text field.

3	Locate the Inp	ut Parameters s	section. In	the table.	enter the f	following sett	ings:

Name	Expression	Value	Description
I_PM	1_PM	4.48E-4 m	Proof mass length
w_PM	w_PM	IE-4 m	Proof mass full width
t_PM	tSi	2E-6 m	Proof mass thickness
l_f	1_f	1.14E-4 m	Length of finger
w_f	w_f	4E-6 m	Width of finger
n_st	n_st	3	Number of self test fingers
n_f	n_f	21	Number of sense fingers
g_f	g_f	IE-6 m	Gap between sense fingers
g_st	g_st	3E-6 m	Gap between self test fingers
x_st	x_st	IE-5 m	Starting position of self test fingers
x_f	x_f	7.2E-5 m	Starting position of sense fingers
w_eh	w_eh	4E-6 m	Etch hole size
p_eh	p_eh	1.8E-5 m	Etch hole period

4 Click 🟢 Build All Objects.

5 Click the **Comextents** button in the **Graphics** toolbar.

Part Link: Spring 1

I In the Geometry toolbar, click \triangle Parts and choose Spring and anchor.

2 In the Settings window for Part Instance, type Part Link: Spring 1 in the Label text field.

Name	Expression	Value	Description
l_sp	l_sp	2.8E-4 m	Spring length
w_sp	w_sp	2E-6 m	Spring width
g_sp	g_sp	IE-6 m	Spring gap
w_sp_conn	w_sp_conn	4E-6 m	Spring connection width
w_f	w_f	4E-6 m	Guard finger width
l_anch_base	l_anch_base	1.7E-5 m	Anchor base length
w_anch_base	w_anch_base	1.7E-5 m	Anchor base width
r_anch	r_anch	3E-6 m	Anchor radius
x_anch	x_anch	1.2E-5 m	Anchor position
t_sp	tSi	2E-6 m	Spring thickness
t_anch	t0x	I.6E-6 m	Anchor thickness
x_sp	1_PM	4.48E-4 m	Position

3 Locate the Input Parameters section. In the table, enter the following settings:

4 Click **Build All Objects**.

Part Link: Spring 2

- I Right-click Part Link: Spring I and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Spring 2 in the Label text field.
- 3 Locate the Input Parameters section. In the table, enter the following settings:

Name	Expression	Value	Description
mirror	0	0	0: no mirror. I: mirror
l_sp	1_sp+10[um]	2.9E-4 m	Spring length
w_anch_base	w_anch_base+10[um]	2.7E-5 m	Anchor base width
x_sp	O[um]	0 m	Position

4 Click 🟢 Build All Objects.

Part Link: Sense Electrodes L

- I In the Geometry toolbar, click \land Parts and choose Electrode array.
- 2 In the Settings window for Part Instance, locate the Input Parameters section.

Name	Expression	Value	Description
LH	0	0	0: RH, I: LH
l_e	l_e_1	I.4E-4 m	Electrode length
w_e	w_f	4E-6 m	Electrode width
l_p	1_p	1.6E-5 m	Pad length
w_p	w_p	8E-6 m	Pad width
r_an	r_an	3E-6 m	Anchor radius
t_e	tSi	2E-6 m	Electrode thickness
t_an	tOx	I.6E-6 m	Anchor thickness
n_e	n_f+1	22	Number of electrodes
p_e	3*(w_f+g_f)	1.5E-5 m	Periodicity
x_e	x_f-w_f-g_f	6.7E-5 m	x position
y_e	w_PM/2+l_f-l_ovrlp	6E-5 m	y position

3 In the table, enter the following settings:

4 In the Label text field, type Part Link: Sense Electrodes L.

- 5 Click 🟢 Build All Objects.
- 6 Click the 🔁 Wireframe Rendering button in the Graphics toolbar.

Part Link: Sense Electrodes R

- I Right-click Part Link: Sense Electrodes L and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Sense Electrodes R in the Label text field.
- 3 Locate the Input Parameters section. In the table, enter the following settings:

Name	Expression	Value	Description
LH	1	I	0: RH, I: LH
l_e	l_e_s	1.2E-4 m	Electrode length
x_e	x_f-2*(w_f+g_f)	6.2E-5 m	x position

4 Click 🟢 Build All Objects.

Part Link: Self Test Electrodes L 1

- I Right-click Part Link: Sense Electrodes R and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Self Test Electrodes L 1 in the Label text field.

Name	Expression	Value	Description
LH	0	0	0: RH, I: LH
n_e	n_st	3	Number of electrodes
p_e	3*w_f+2*g_f+g_st	1.7E-5 m	Periodicity
x_e	x_f-2*(w_f+g_f)	6.2E-5 m	x position

3 Locate the Input Parameters section. In the table, enter the following settings:

4 Click 📳 Build All Objects.

5 In the table, enter the following settings:

Name	Expression	Value	Description
x_e	x_st-w_f-g_f	5E-6 m	x position

6 Click 🟢 Build All Objects.

Part Link: Self Test Electrodes L 2

- I Right-click Part Link: Self Test Electrodes L I and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Self Test Electrodes L2 in the Label text field.
- 3 Locate the Input Parameters section. In the table, enter the following settings:

Name	Expression	Value	Description
l_e	1_e_1	I.4E-4 m	Electrode length
x_e	l_PM-(x_st+w_f+g_f)- (n_st-1)*(3*w_f+2* g_f+g_st)-w_f	3.95E-4 m	x position

4 Click 📑 Build All Objects.

Part Link: Self Test Electrodes R I

- I Right-click Part Link: Self Test Electrodes L 2 and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Self Test Electrodes R 1 in the Label text field.
- 3 Locate the Input Parameters section. In the table, enter the following settings:

Name	Expression	Value	Description
LH	1	I	0: RH, 1: LH
x_e	x_st-w_f-g_f+2*(w_f+g_f)	1.5E-5 m	x position

4 Click 📗 Build All Objects.

Part Link: Self Test Electrodes R 2

- I Right-click Part Link: Self Test Electrodes R I and choose Duplicate.
- 2 In the Settings window for Part Instance, type Part Link: Self Test Electrodes R 2 in the Label text field.
- 3 Locate the Input Parameters section. In the table, enter the following settings:

Name	Expression	Value	Description
l_e	l_e_s	I.2E-4 m	Electrode length
x_e	l_PM-(x_st+w_f+g_f)- (n_st-1)*(3*w_f+2* g_f+g_st)-w_f+2*(w_f+ g_f)	4.05E-4 m	x position

4 Click 📗 Build All Objects.

5 Click the $\sqrt{-}$ Go to Default View button in the Graphics toolbar.

Air box

- I In the **Geometry** toolbar, click **[]** Block.
- 2 In the Settings window for Block, type Air box in the Label text field.
- 3 Locate the Size and Shape section. In the Width text field, type 1_polySi+40[um].
- 4 In the **Depth** text field, type hw_polySi+20[um].
- 5 In the **Height** text field, type 10[um].
- 6 Locate the **Position** section. In the **x** text field, type -1_spAssm-20[um].
- 7 In the z text field, type -t0x.
- 8 Click to expand the Layers section. In the table, enter the following settings:

Layer name	Thickness (m)
Layer 1	tOx
Layer 2	tSi

9 Click 🟢 Build All Objects.

IO In the Model Builder window, click Geometry I.

II In the Settings window for Geometry, locate the Units section.

- **12** From the **Length unit** list, choose **µm**.
- **I3** In the **Model Builder** window, click **Air box (blk1)**.

14 In the Settings window for Block, click 📗 Build All Objects.

IS Click the **J Go to Default View** button in the **Graphics** toolbar.

Ground plane

- I In the Geometry toolbar, click · Work Plane.
- 2 In the Settings window for Work Plane, type Ground plane in the Label text field.
- **3** Locate the **Plane Definition** section. In the **z-coordinate** text field, type -t0x.

Ground plane (wp1)>Plane Geometry

- I In the Model Builder window, click Plane Geometry.
- **2** Click the $4 \rightarrow$ **Zoom Extents** button in the **Graphics** toolbar.

Ground plane (wp1)>Rectangle 1 (r1)

- I In the Work Plane toolbar, click Rectangle.
- 2 In the Settings window for Rectangle, locate the Size and Shape section.
- **3** In the **Width** text field, type 1_PM.
- 4 In the Height text field, type w_PM/2+1_f.
- 5 Click 틤 Build Selected.

Extrude I (extI)

- I In the Model Builder window, right-click Geometry I and choose Extrude.
- 2 In the Settings window for Extrude, locate the Distances section.
- **3** In the table, enter the following settings:

Distances (µm)

t0x

4 Click 📄 Build Selected.

Part Link: Proof mass (pil)

- I In the Model Builder window, click Part Link: Proof mass (pil).
- 2 In the Settings window for Part Instance, click to expand the Domain Selections section.
- **3** Click to select row number 1 in the table.
- 4 Click New Cumulative Selection.
- 5 In the New Cumulative Selection dialog box, type Polysilicon in the Name text field.
- 6 Click OK.
- 7 In the Settings window for Part Instance, click to expand the Boundary Selections section.

8 Click New Cumulative Selection.

9 In the **New Cumulative Selection** dialog box, type **Proof** mass boundaries in the **Name** text field.

IO Click OK.

II In the Settings window for Part Instance, locate the Boundary Selections section.

12 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Proof Mass + Fingers Seq		\checkmark	Proof mass boundaries

Part Link: Spring 1 (pi2)

I In the Model Builder window, click Part Link: Spring I (pi2).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Spring + anchor		\checkmark	Polysilicon

4 Locate the **Boundary Selections** section. In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Spring + anchor		\checkmark	Proof mass boundaries

Part Link: Spring 2 (pi3)

I In the Model Builder window, click Part Link: Spring 2 (pi3).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Spring + anchor			Polysilicon

4 Locate the **Boundary Selections** section. In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Spring + anchor		\checkmark	Proof mass boundaries

Part Link: Sense Electrodes L (pi4)

I In the Model Builder window, click Part Link: Sense Electrodes L (pi4).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

- **4** Locate the **Boundary Selections** section. Click to select row number 1 in the table.
- 5 Click New Cumulative Selection.
- 6 In the New Cumulative Selection dialog box, type Sense left boundaries in the Name text field.
- 7 Click OK.

Part Link: Sense Electrodes R (pi5)

- I In the Model Builder window, click Part Link: Sense Electrodes R (pi5).
- 2 In the Settings window for Part Instance, locate the Domain Selections section.
- **3** In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

- 4 Locate the **Boundary Selections** section. Click to select row number 1 in the table.
- 5 Click New Cumulative Selection.
- 6 In the New Cumulative Selection dialog box, type Sense right boundaries in the Name text field.
- 7 Click OK.

Part Link: Self Test Electrodes L 1 (pi6)

- I In the Model Builder window, click Part Link: Self Test Electrodes L I (pi6).
- 2 In the Settings window for Part Instance, locate the Boundary Selections section.
- 3 Click New Cumulative Selection.
- 4 In the New Cumulative Selection dialog box, type Self test left boundaries in the Name text field.
- 5 Click OK.
- 6 In the Settings window for Part Instance, locate the Boundary Selections section.
- 7 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array			Self test left boundaries

Part Link: Self Test Electrodes L 2 (pi7)

- I In the Model Builder window, expand the Component I (compl)>Geometry I> Cumulative Selections node, then click Component I (compl)>Geometry I> Part Link: Self Test Electrodes L 2 (pi7).
- 2 In the Settings window for Part Instance, locate the Domain Selections section.
- **3** In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

4 Locate the **Boundary Selections** section. In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Self test left boundaries

Part Link: Self Test Electrodes R 1 (pi8)

I In the Model Builder window, click Part Link: Self Test Electrodes R I (pi8).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

4 Click to select row number 1 in the table.

5 Locate the Boundary Selections section. Click New Cumulative Selection.

- 6 In the New Cumulative Selection dialog box, type Self test right boundaries in the Name text field.
- 7 Click OK.
- 8 In the Settings window for Part Instance, locate the Boundary Selections section.
- **9** In the table, enter the following settings:

Name	Кеер	Physics	Contribute to	
Electrode array		\checkmark	Self test right boundaries	

Part Link: Self Test Electrodes R 2 (pi9)

I In the Model Builder window, click Part Link: Self Test Electrodes R 2 (pi9).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

4 Locate the **Boundary Selections** section. In the table, enter the following settings:

Name	Кеер	Physics	Contribute to	
Electrode array			Self test right boundaries	

Part Link: Self Test Electrodes L 1 (pi6)

I In the Model Builder window, click Part Link: Self Test Electrodes L I (pi6).

2 In the Settings window for Part Instance, locate the Domain Selections section.

3 In the table, enter the following settings:

Name	Кеер	Physics	Contribute to
Electrode array		\checkmark	Polysilicon

Ground plane (wp1)

In the Model Builder window, collapse the Component I (compl)>Geometry I> Ground plane (wpl) node.

Cumulative Selections

- I In the Model Builder window, collapse the Component I (compl)>Geometry l> Cumulative Selections node.
- 2 In the Model Builder window, collapse the Geometry I node.

DEFINITIONS

Symmetry plane

- I In the **Definitions** toolbar, click here is a second sec
- 2 In the Settings window for Box, locate the Geometric Entity Level section.
- 3 From the Level list, choose Boundary.
- 4 Locate the Box Limits section. In the y minimum text field, type -0.1.
- 5 In the **y maximum** text field, type 0.1.
- 6 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.
- 7 In the Label text field, type Symmetry plane.

Anchor plane

- I In the **Definitions** toolbar, click **The Box**.
- 2 In the Settings window for Box, type Anchor plane in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- 4 Locate the **Box Limits** section. In the **z minimum** text field, type -t0x*1.01.
- 5 In the z maximum text field, type -t0x*0.99.
- 6 Locate the **Output Entities** section. From the **Include entity if** list, choose **Entity inside box**.

Meshing plane

- I In the **Definitions** toolbar, click **The Box**.
- 2 In the Settings window for Box, type Meshing plane in the Label text field.
- 3 Locate the Geometric Entity Level section. From the Level list, choose Boundary.
- 4 Locate the **Box Limits** section. In the **z minimum** text field, type -t0x*0.01.
- 5 In the z maximum text field, type t0x*0.01.
- 6 Locate the Output Entities section. From the Include entity if list, choose Entity inside box.